



Product Overview

NDDP010N25AZ: Power MOSFET, 250 V, 10 A, 420 mΩ, Single N-Channel

For complete documentation, see the data sheet

Product Description

This N-Channel Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize input capacitance and gate charge. This device is suitable for applications with low gate charge driving requirements.

Features

- High Speed Switching
- ESD Diode-Protected Gate
- Low Gate Charge
- 100% Avalanche Tested
- Pb-Free, Halogen Free and RoHS Compliance

Benefits

- Reduces dynamic power losses
- ESD resistance
- Ease of drive, faster turn-on
- Voltage overstress safeguard
- Environment friendliness

Applications

- Battery Protection
- Motor Drive
- Primary Side Switch
- Secondary Side Synchronous Rectification

End Products

- Multi-Cells Battery Pack (ESS, E-Bike, P-Tool)
- Other Motor
- Power Supply

Part Electrical Specifications

Product	Compliance	Status	Channel Polarity	Configuration	$V_{DS(BR)}$ Min (V)	V_{GS} Max (V)	$V_{GS(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$r_{DS(on)}$ Max @ $V_{GS} = 2.5$ V (m)	$r_{DS(on)}$ Max @ $V_{GS} = 4.5$ V (m)	$r_{DS(on)}$ Max @ $V_{GS} = 10$ V (m)	Q_g Typ @ $V_{GS} = 4.5$ V (nC)	Q_g Typ @ $V_{GS} = 10$ V (nC)	Q_{gd} Typ @ $V_{GS} = 4.5$ V (nC)	Q_{rr} Typ (nC)	C_{iss} Typ (pF)	C_{oss} Typ (pF)	C_{rss} Typ (pF)	Packaging Type
NDDP010N25AZ-1H	Pb-free Halide free	Active	N-Channel	Single	250	30	4.5	10	52			420		16		540	980	80	25	IPAK / TP
NDDP010N25AZT4H	Pb-free Halide free	Active	N-Channel	Single	250	30	4.5	10	52			420		16		540	980	80	25	DPAK / TP-FA

For more information please contact your local sales support at www.onsemi.com

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